

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S72	932	etch\$4 and ((carbon C) adj dop\$4 with (glass low adj (k dielectric)))	US-PGPU B; USPAT	OR	ON	2006/02/16 22:15
S74	0	("2003/0211723").URPN.	USPAT	OR	ON	2006/02/16 22:16
S73	1	etch\$4 and ((carbon C) adj dop\$4 adj glass adj low adj (k dielectric))	US-PGPU B; USPAT	OR	ON	2006/02/16 22:18
S76	210	etch\$4 with SiOC	US-PGPU B; USPAT	OR	ON	2006/02/16 22:30
S77	49	etch\$4 with SiOC with low	US-PGPU B; USPAT	OR	ON	2006/02/16 22:31
S79	5	("20030068582" "20040106293" "20040171273" "6613689" "6712983"). PN. OR ("6967171"). URPN.	US-PGPU B; USPAT; USOCR	OR	ON	2006/02/16 22:32
S78	1	("2004/0106293").URPN.	USPAT	OR	ON	2006/02/16 22:32
S75	20	etch\$4 and carbon-doped adj glass	US-PGPU B; USPAT	OR	ON	2006/02/16 22:36
S83	2	carbon near content near teos	US-PGPU B; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 23:15

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S82	0	carbon near content near teos	EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/16 23:15
S81	20106	carbon near content neat teos	EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/16 23:15
S84	182	TEOS with (SiOC carbon-dop\$4 C-dop\$4 (carbon C) adj dop\$4)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/17 12:15
S85	155	TEOS with (SiOC (carbon-dop\$4 C-dop\$4 (carbon C) adj dop\$4 near2 glass))	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/17 12:16
S86	17	TEOS near (SiOC (carbon-dop\$4 C-dop\$4 (carbon C) adj dop\$4 near2 glass))	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/17 12:21

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S87	20	TEOS near (siliconoxycarbide silicon adj oxycarbide SiOC carbon-dop\$4 C-dop\$4 (carbon C) adj dop\$4 near2 (glass oxide) CDO black adj diamond) NOT S86	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/17 12:27
S88	48	TEOS near3 (siliconoxycarbide silicon adj oxycarbide SiOC carbon-dop\$4 C-dop\$4 (carbon C) adj dop\$4 near2 (glass oxide) CDO black adj diamond) NOT (S86 S87)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/17 12:34
S90	68	S85 NOT (S86 S87 S88 S89)	US-PGPU B; USPAT	OR	ON	2006/02/17 12:38
S89	35	TEOS near6 (siliconoxycarbide silicon adj oxycarbide SiOC carbon-dop\$4 C-dop\$4 (carbon C) adj dop\$4 near2 (glass oxide) CDO black adj diamond) NOT (S86 S87 S88)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/17 12:38
S92	26	S84 not S85	US-PGPU B; USPAT; USOCR	OR	ON	2006/02/17 12:58
S91	5	("6051503" "6191043" "6242165" "6261962"). PN. OR ("6451673"). URPN.	US-PGPU B; USPAT; USOCR	OR	ON	2006/02/17 12:58

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S80	89	etch\$4 and (SiOC carbon-doped)	EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 22:45
S95	31	S93 not S94	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 22:47
S94	7	etch\$4 near (SiOC carbon-doped CORAL) with (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 22:47
S97	18	S96 not S93	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 22:56
S93	38	etch\$4 with (SiOC carbon-doped CORAL) with (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 22:56

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S98	38	etch\$4 same (SiOC carbon-doped CORAL) same (N2 "N.sub.2" nitrogen) not S96	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 22:58
S96	56	etch\$4 with (SiOC carbon-doped CORAL) same (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 23:05
S101	1	("6383931").PN.	DERWEN T	OR	OFF	2006/02/20 23:15
S100	1	("6410437").PN.	DERWEN T	OR	OFF	2006/02/20 23:15
S99	1	etch\$4 with (SiOC carbon-doped CORAL\$) same (N2 "N.sub.2" nitrogen) not S96	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 23:16
S104	84	etch\$4 with (SiOC carbon-doped CORAL\$) and etch\$4 with (N2 "N.sub.2" nitrogen) not (S96 S98)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/02/20 23:20

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S10 3	257	etch\$4 same (SiOC carbon-doped CORAL\$) and etch\$4 same (N2 "N.sub.2" nitrogen) not (S96 S98)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/02/20 23:20
S10 2	5	etch\$4 same (SiOC carbon-doped CORAL\$) same (N2 "N.sub.2" nitrogen) not (S96 S98)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/02/20 23:20
S10 5	1	(US-6168726-\$).did.	USPAT	OR	ON	2006/02/20 23:39
S10 6	1	S105 and S104	USPAT	OR	ON	2006/02/20 23:40
S10 8	0	S107 and coral\$	US-PGPU B; USPAT	OR	ON	2006/02/21 12:20
S10 7	1	("6284149").PN.	USPAT	OR	OFF	2006/02/21 12:20
S10 9	0	S107 and (carbon-doped SiOC black adj diamond)	US-PGPU B; USPAT	OR	ON	2006/02/21 12:21
S56	0	S52 and ((C4F8 "C.sub.4 F.sub.8" perfluorobutane octafluorobutane) with (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane) with (N2 "N.sub.2" nitrogen))	US-PGPU B; USPAT	OR	ON	2006/02/21 12:31

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S11 0	2	(carbon-doped SiOC black adj diamond) and ((C4F8 "C.sub.4 F.sub.8" perfluoro\$5but?ne octafluoro\$5but?ne) with (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub. 2" difluoromethane) with (N2 "N.sub.2" nitrogen))	US-PGPU B; USPAT	OR	ON	2006/02/21 12:33
S11 2	36	(C5F8 "C.sub.5 F.sub.8" \$4fluorocyclopentene) same (N2 "N.sub.2" nitrogen) same etch\$4 not S111	US-PGPU B; USPAT	OR	ON	2006/06/17 17:04
S11 1	24	(C5F8 "C.sub.5 F.sub.8" \$4fluorocyclopentene) with (N2 "N.sub.2" nitrogen) same etch\$4	US-PGPU B; USPAT	OR	ON	2006/06/17 17:04
S11 5	3	S114 not S113	US-PGPU B; USPAT	OR	ON	2006/06/17 17:33

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S11 3	50	(US-20020016085-\$ or US-20010026956-\$ or US-20030162407-\$ or US-20030024902-\$ or US-20030045101-\$ or US-20020108929-\$ or US-20020025693-\$ or US-20020140101-\$ or US-20020105084-\$).did. or (US-6207577-\$ or US-6380091-\$ or US-6485988-\$ or US-6368979-\$ or US-6541396-\$ or US-6387775-\$ or US-6451673-\$ or US-6153514-\$ or US-6251770-\$ or US-6284149-\$ or US-6455411-\$ or US-6472317-\$ or US-6506680-\$ or US-6376367-\$ or US-6350674-\$ or US-6693042-\$ or US-6326307-\$ or US-5843847-\$ or US-6316349-\$ or US-6417090-\$ or US-6211092-\$ or US-6410437-\$ or US-6743732-\$ or US-6395631-\$ or US-6207554-\$ or US-6297163-\$).did. or (US-6074959-\$ or US-5021121-\$ or US-5269879-\$ or US-6117786-\$ or US-6696366-\$ or US-6670276-\$ or US-6090304-\$ or US-6613689-\$ or US-5254213-\$ or US-6465335-\$ or US-6348407-\$ or US-6313538-\$).did. or (JP-2002083798-\$).did. or	US-PGPU B; USPAT; JPO; DERWEN T	OR	ON	2006/06/17 17:33
9/7/07 4:29:21 PM C:\Documents and Settings\jolsen\My Documents\EAST\Workspaces\09 series\109820695.wsp		Page 8				

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S11 6	3	S114 and low adj (k dielectric)	US-PGPU B; USPAT	OR	ON	2006/06/17 17:41
S11 4	5	(US-6455411-\$ or US-6764606-\$ or US-6607675-\$ or US-6465359-\$ or US-6316349-\$).did.	USPAT	OR	ON	2006/06/17 17:41
S11 9	0	S114 and (carbon-dop\$\$ (carbon C) adj dop\$4)	US-PGPU B; USPAT	OR	ON	2006/06/17 17:43
S11 8	3	S114 and (carbon -dop\$\$ (carbon C) adj dop\$4)	US-PGPU B; USPAT	OR	ON	2006/06/17 17:43
S11 7	3	S114 and (low-k low adj (k dielectric))	US-PGPU B; USPAT	OR	ON	2006/06/17 17:43
S12 1	7	S120 and dual	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 19:18
S12 4	7	S120 and MHz	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 19:21
S12 0	12	("20020001952" "4427516" "4857140" "5242538" "5814563" "6114259" "6165891" "6251770" "6340435" "6346490" "6350670" "6368979").PN.	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 19:29
S12 6	0	S125 and dual adj frequency	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 19:30

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S12 5	11	(("6095084") or ("6077384") or ("6074512") or ("6071372") or ("6063233") or ("6054013") or ("6036878") or ("6026762") or ("6020686") or ("5976308") or ("5900064")).PN.	USPAT	OR	OFF	2006/06/18 19:30
S12 3	2	S120 and parallel adj plate	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 19:30
S12 2	0	S120 and dual adj frequency	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 19:30
S12 7	5	S125 and parallel adj plate	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/18 21:42
S12 8	18	(C4F8 "C4.sub.4 F.sub.8" \$4fluorbutene \$4fluorocyclobutane) and (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub. 2" difluoromethane methylene-fluoride) and (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 21:46
S13 3	2	S130 and (C4F8 "C.sub.4 F.sub.8" \$4fluorobutene \$4fluorocyclobutane) near2 (CH2F2 CF2H2 "CH. sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane methylene-\$2fluoride) near2 (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 21:48

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S13 0	291	S129 and etch\$4	US-PGPU B; USPAT	OR	ON	2006/06/18 21:48
S13 2	40	S130 and (C4F8 "C.sub.4 F.sub.8" \$4fluorobutene \$4fluorocyclobutane) with (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane methylene-\$2fluoride) with (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 21:50
S12 9	631	(C4F8 "C.sub.4 F.sub.8" \$4fluorobutene \$4fluorocyclobutane) and (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane methylene-\$2fluoride) and (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 22:05
S13 5	631	(C4F8 "C.sub.4 F.sub.8" \$4fluorobutene "perfluoro-1-butene" "perfluoro-2-butene" \$4fluorocyclobutane) and (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane methylene-\$2fluoride) and (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 22:06
S13 4	631	(C4F8 "C.sub.4 F.sub.8" \$4fluorobutene \$4fluoro-1-butene \$4fluoro-2-butene \$4fluorocyclobutane) and (CH2F2 CF2H2 "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane methylene-\$2fluoride) and (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 22:06
S13 6	42	S131 not S132	US-PGPU B; USPAT	OR	ON	2006/06/18 22:12

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S13 1	82	S130 and (C4F8 "C.sub.4 F.sub.8" \$4fluorobutene \$4fluorocyclobutane) same (CH2F2 CF2H2 "CH. sub.2 F.sub.2" "CF.sub.2 H.sub.2" difluoromethane methylene-\$2fluoride) same (N2 "N.sub.2" nitrogen)	US-PGPU B; USPAT	OR	ON	2006/06/18 22:12
S13 7	49	dual adj frequency with (plasma etch\$4) and (SiO2 "SiO.sub.2" oxide) with (SiN Si3N4 "Si.sub.3 N.sub.4" nitride) with selectiv\$4	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/06/24 19:53
S13 8	3	dual adj frequency with (plasma etch\$4) same (SiO2 "SiO.sub.2" oxide) with (SiN Si3N4 "Si.sub.3 N.sub.4" nitride) with selectiv\$4	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2006/06/24 19:54

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S13 9	610521	(method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (C-doped carbon-doped dop\$4 near (C carbon)) and (oxygen-free without near (oxygen "O.sub.2" O2)) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead electrode	US-PGPU B; USPAT	OR	ON	2007/09/04 17:40
S14 0	0	(method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (C-doped carbon-doped dop\$4 near (C carbon)) and (oxygen-free without near (oxygen "O.sub.2" O2)) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead adj electrode	US-PGPU B; USPAT	OR	ON	2007/09/04 17:41

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S14 2	4	(method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub. 8") and flow near (rate ratio)	US-PGPU B; USPAT	OR	ON	2007/09/04 17:44
S14 1	0	(method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub. 8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead adj electrode	US-PGPU B; USPAT	OR	ON	2007/09/04 17:44
L3	30	((S) near2 (SADJADI)). INV.	US-PGPU B; USPAT	OR	ON	2007/09/07 15:53
L2	30	((HELEN) near2 (ZHU)). INV.	US-PGPU B; USPAT	OR	ON	2007/09/07 15:53
L1	10	((SI) near2 (LI)).INV.	US-PGPU B; USPAT	OR	ON	2007/09/07 15:53
L5	2	((BRYAN) near2 (HELMER)).INV.	US-PGPU B; USPAT	OR	ON	2007/09/07 15:54
L4	30	((S) near2 (SADJADI)). INV.	US-PGPU B; USPAT	OR	ON	2007/09/07 15:54
L7	25	((JAMES) near2 (TIETZ)). INV.	US-PGPU B; USPAT	OR	ON	2007/09/07 15:55

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L6	61	1 2 3 4 5	US-PGPU B; USPAT	OR	ON	2007/09/07 15:55
L9	1	1 and 2 and 3 and 5 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:56
L8	84	1 2 3 5 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:56
L16	1	5 and 3	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L15	1	5 and 2	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L14	2	1 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L13	1	1 and 5	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L12	5	1 and 3	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L11	3	1 and 2	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L10	1	1 and 2 and 3 and (5 7)	US-PGPU B; USPAT	OR	ON	2007/09/07 15:57
L19	1	2 and 3 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:58
L18	1	1 and 2 and 3 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:58
L17	1	5 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:58

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L21	1	2 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 15:59
L20	4	2 and 3	US-PGPU B; USPAT	OR	ON	2007/09/07 15:59
L22	2	3 and 7	US-PGPU B; USPAT	OR	ON	2007/09/07 16:00

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L23	0	"PG-Pubs Interference Search"	US-PGPU B	OR	ON	2007/09/07 16:01
L24	0	((method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (C-doped carbon-doped dop\$4 near (C carbon)) and (oxygen-free without near (oxygen "O.sub.2" O2)) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead). clm.	US-PGPU B	OR	ON	2007/09/07 16:09
L26	0	((method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (C-doped carbon-doped dop\$4 near (C carbon)) and (oxygen-free without near (oxygen "O.sub.2" O2)) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead)	US-PGPU B; USPAT	OR	ON	2007/09/07 16:10

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L25	0	((method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (C-doped carbon-doped dop\$4 near (C carbon)) and (oxygen-free without near (oxygen "O.sub.2" O2)) and (nitrogen N2 "N.sub. 2") and (C5F8 "C.sub.5 F. sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead)	US-PGPU B	OR	ON	2007/09/07 16:10
L27	0	((method process) with etch\$4 with (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (C-doped carbon-doped dop\$4 near (C carbon)) and (oxygen-free without near (oxygen "O.sub.2" O2)) and (nitrogen N2 "N.sub. 2") and (C5F8 "C.sub.5 F. sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2007/09/07 16:11

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L30	0	(etch\$4 same (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C. sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2007/09/07 16:12
L29	0	(etch\$4 same (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C. sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead)	US-PGPU B	OR	ON	2007/09/07 16:12
L28	0	(etch\$4 same (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C. sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency and parallel adj plate and showerhead).clm.	US-PGPU B	OR	ON	2007/09/07 16:12

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L31	0	(etch\$4 same (Iow-k low adj dielectric) and selectiv\$4 same (mask\$4 resist photoresist) and semiconductor and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2007/09/07 16:14
L32	1	(etch\$4 same (Iow-k low adj dielectric) and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow near (rate ratio) and dual adj frequency)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2007/09/07 16:17
L33	2	(etch\$4 and (Iow-k low adj dielectric) and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow with (rate ratio) and dual adj frequency)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2007/09/07 16:18
L34	32	(etch\$4 and (Iow-k low adj dielectric) and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow with (rate ratio))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TD B	OR	ON	2007/09/07 16:19

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L37	0	(etch\$4 and (low-k low adj dielectric) and (mask\$4 resist photoresist) and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8")).clm.	US-PGPU B	OR	ON	2007/09/07 16:20
L36	0	(etch\$4 and (low-k low adj dielectric) and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8")).clm.	US-PGPU B	OR	ON	2007/09/07 16:20
L38	0	(etch\$4 and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow with (rate ratio)).clm.	US-PGPU B	OR	ON	2007/09/07 16:22
L35	0	(etch\$4 and (low-k low adj dielectric) and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow with (rate ratio)).clm.	US-PGPU B	OR	ON	2007/09/07 16:22
L42	0	(etch\$4 and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8")).clm.	US-PGPU B	OR	ON	2007/09/07 16:23
L41	0	(etch\$4 and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8")).clm.	US-PGPU B	OR	ON	2007/09/07 16:23
L40	0	(etch\$4 and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8")).clm.	US-PGPU B	OR	ON	2007/09/07 16:23

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L39	0	(etch\$4 and (mask\$4 resist photoresist) and plasma and (nitrogen N2 "N.sub.2") and (C5F8 "C.sub.5 F.sub.8") and flow and (rate ratio)).clm.	US-PGPU B	OR	ON	2007/09/07 16:23
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